BC856ALT1 Series

Preferred Devices

General Purpose Transistors

PNP Silicon

Features

- Pb−Free Packages are Available

ON Semiconductor®

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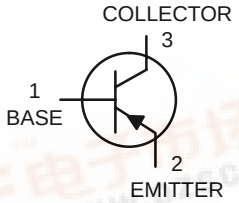
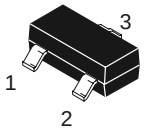




SOT−23
CASE 318
STYLE 6

MAXIMUM RATINGS (T_A = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Collector-Emitter Voltage	BC856 BC857 BC858, BC859	V_{CEO}	−65 −45 −30	V
Collector-Base Voltage	BC856 BC857 BC858, BC859	V_{CBO}	−80 −50 −30	V
Emitter−Base Voltage		V_{EBO}	−5.0	V
Collector Current − Continuous		I_C	−100	mAdc

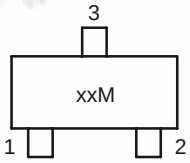
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR−5 Board, (Note 1) T_A = 25°C Derate above 25°C	P_D	225 1.8	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate, (Note 2) T_A = 25°C Derate above 25°C	P_D	300 2.4	mW mW/°C
Thermal Resistance, Junction−to−Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature	T_J, T_{stg}	−55 to +150	°C

1. FR−5 = 1.0 x 0.75 x 0.062 in.
2. Alumina = 0.4 x 0.3 x 0.024 in 99.5% alumina.

MARKING DIAGRAM



xx = Device Code
M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Collector−Emitter Breakdown Voltage (I_C = −10 mA)	BC856 Series	$V_{(BR)CEO}$	−65	−	−	V
	BC857 Series		−45	−	−	
	BC858, BC859 Series		−30	−	−	
Collector−Emitter Breakdown Voltage (I_C = −10 μA, V_{EB} = 0)	BC856 Series	$V_{(BR)CES}$	−80	−	−	V
	BC857A, BC857B Only		−50	−	−	
	BC858, BC859 Series		−30	−	−	
Collector−Base Breakdown Voltage (I_C = −10 μA)	BC856 Series	$V_{(BR)CBO}$	−80	−	−	V
	BC857 Series		−50	−	−	
	BC858, BC859 Series		−30	−	−	
Emitter−Base Breakdown Voltage (I_E = −1.0 μA)	BC856 Series	$V_{(BR)EBO}$	−5.0	−	−	V
	BC857 Series		−5.0	−	−	
	BC858, BC859 Series		−5.0	−	−	
Collector Cutoff Current (V_{CB} = −30 V)		I_{CBO}	−	−	−15	nA
(V_{CB} = −30 V, T_A = 150°C)			−	−	−4.0	μA
ON CHARACTERISTICS						
DC Current Gain (I_C = −10 μA, V_{CE} = −5.0 V)	BC856A, BC857A, BC858A	h_{FE}	−	90	−	−
	BC856B, BC857B, BC858B		−	150	−	
	BC857C, BC858C		−	270	−	
(I_C = −2.0 mA, V_{CE} = −5.0 V)	BC856A, BC857A, BC858A		125	180	250	
	BC856B, BC857B, BC858B, BC859B		220	290	475	
	BC857C, BC858C, BC859C		420	520	800	
Collector−Emitter Saturation Voltage		$V_{CE(sat)}$				V
(I_C = −10 mA, I_B = −0.5 mA)			−	−	−0.3	
(I_C = −100 mA, I_B = −5.0 mA)			−	−	−0.65	
Base−Emitter Saturation Voltage		$V_{BE(sat)}$				V
(I_C = −10 mA, I_B = −0.5 mA)			−	−0.7	−	
(I_C = −100 mA, I_B = −5.0 mA)			−	−0.9	−	
Base−Emitter On Voltage		$V_{BE(on)}$				V
(I_C = −2.0 mA, V_{CE} = −5.0 V)			−0.6	−	−0.75	
(I_C = −10 mA, V_{CE} = −5.0 V)			−	−	−0.82	
SMALL−SIGNAL CHARACTERISTICS						
Current−Gain − Bandwidth Product (I_C = −10 mA, V_{CE} = −5.0 Vdc, f = 100 MHz)		f_T	100	−	−	MHz
Output Capacitance (V_{CB} = −10 V, f = 1.0 MHz)		C_{ob}	−	−	4.5	pF
Noise Figure		NF				dB
(I_C = −0.2 mA, V_{CE} = −5.0 Vdc, R_S = 2.0 kΩ, f = 1.0 kHz, BW = 200 Hz)						
	BC856, BC857, BC858 Series		−	−	10	
	BC859 Series		−	−	4.0	

BC857/BC858/BC859

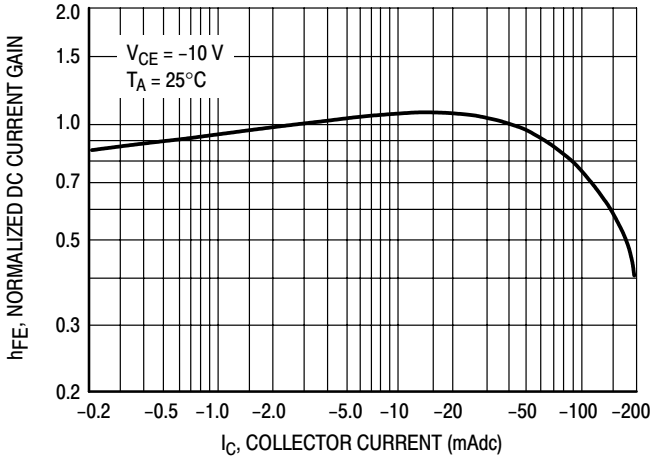


Figure 1. Normalized DC Current Gain

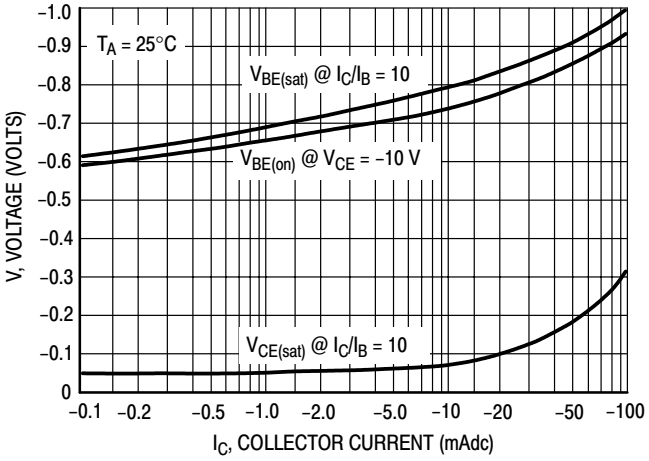


Figure 2. “Saturation” and “On” Voltages

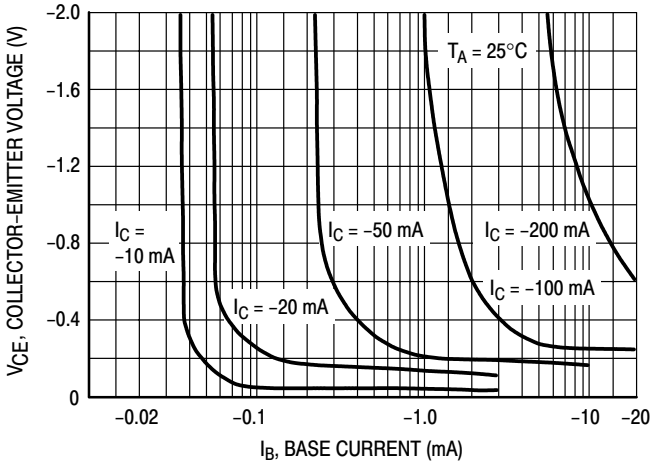


Figure 3. Collector Saturation Region

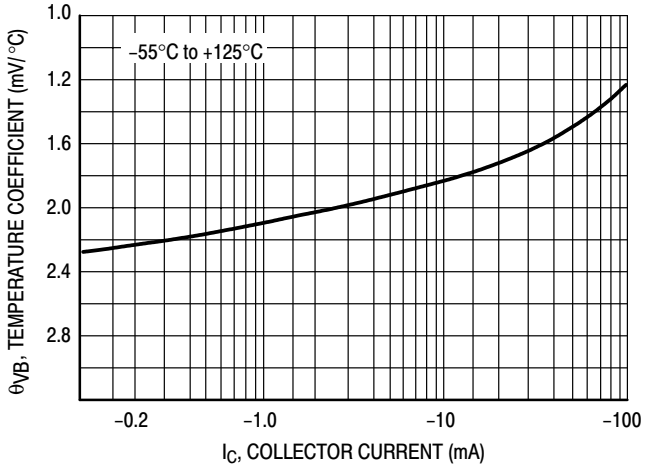


Figure 4. Base−Emitter Temperature Coefficient

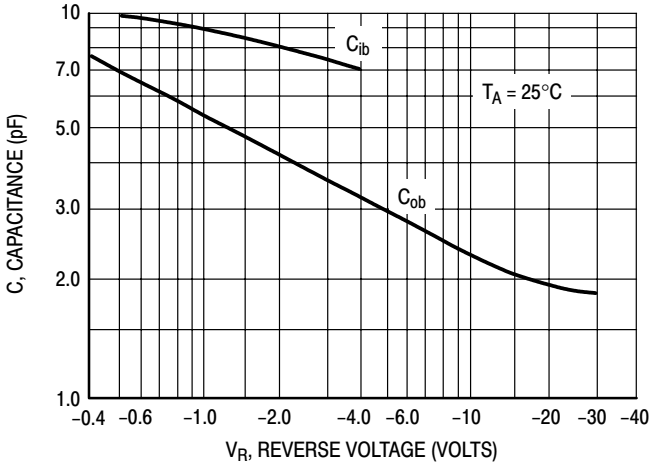


Figure 5. Capacitances

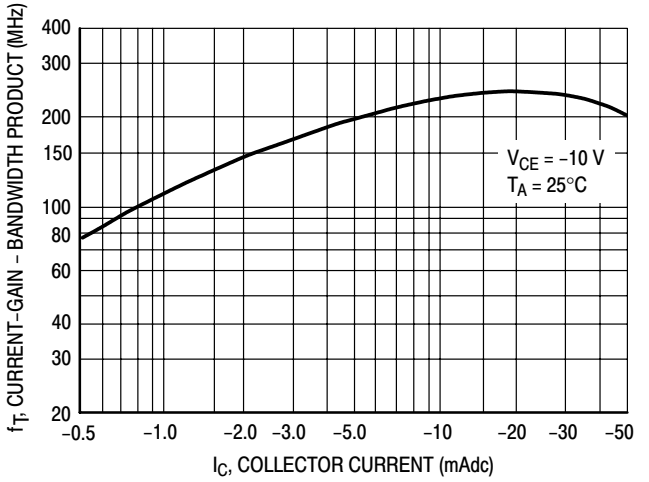


Figure 6. Current−Gain − Bandwidth Product

BC856

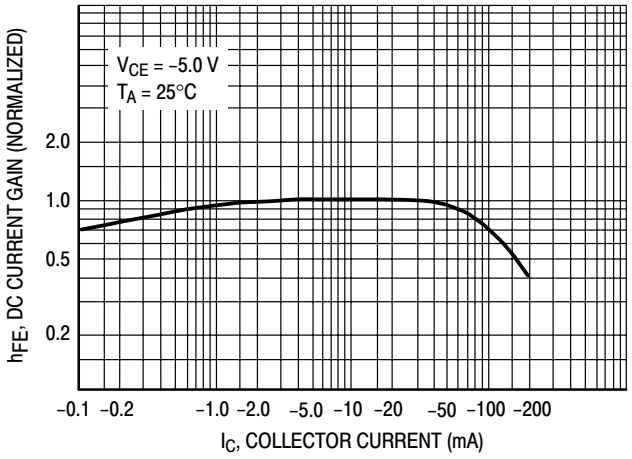


Figure 7. DC Current Gain

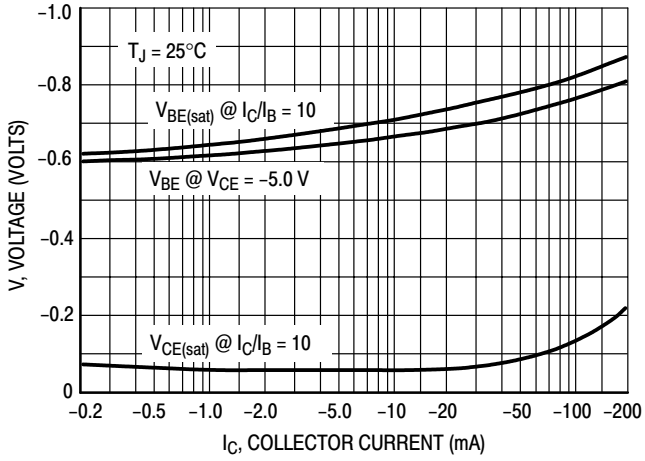


Figure 8. “On” Voltage

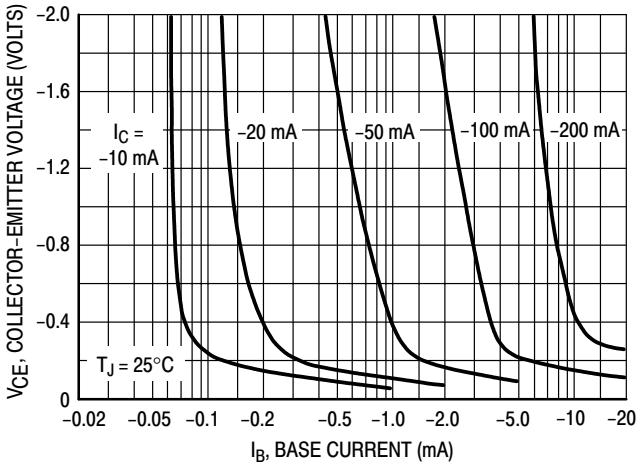


Figure 9. Collector Saturation Region

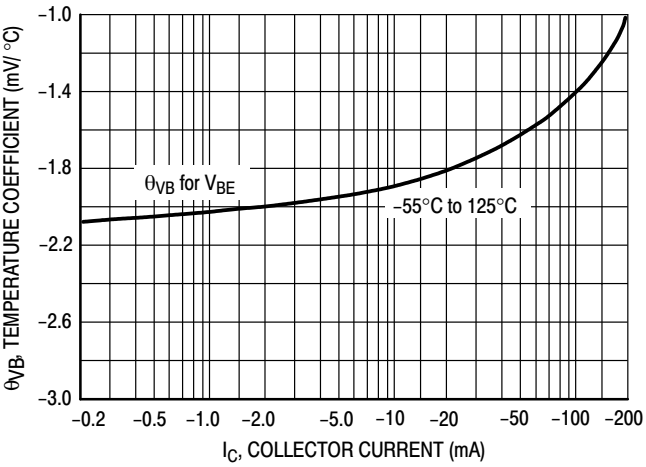


Figure 10. Base−Emitter Temperature Coefficient

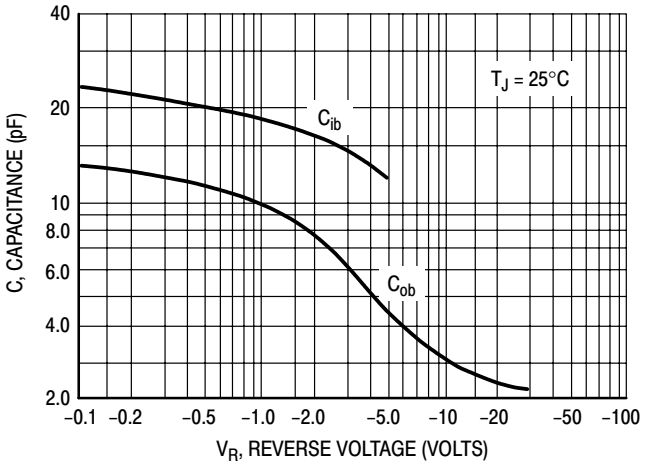


Figure 11. Capacitance

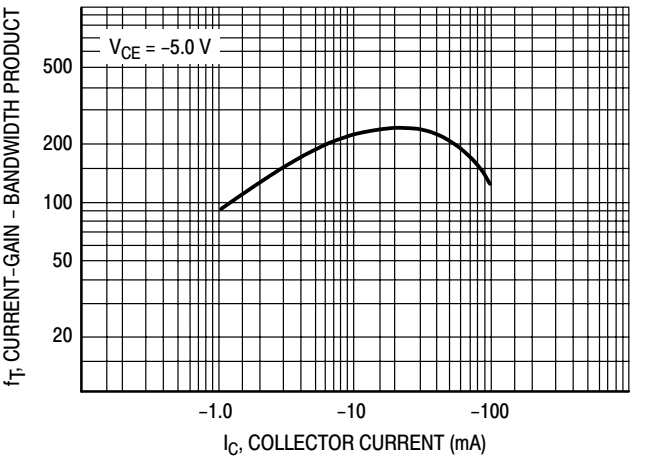


Figure 12. Current−Gain − Bandwidth Product

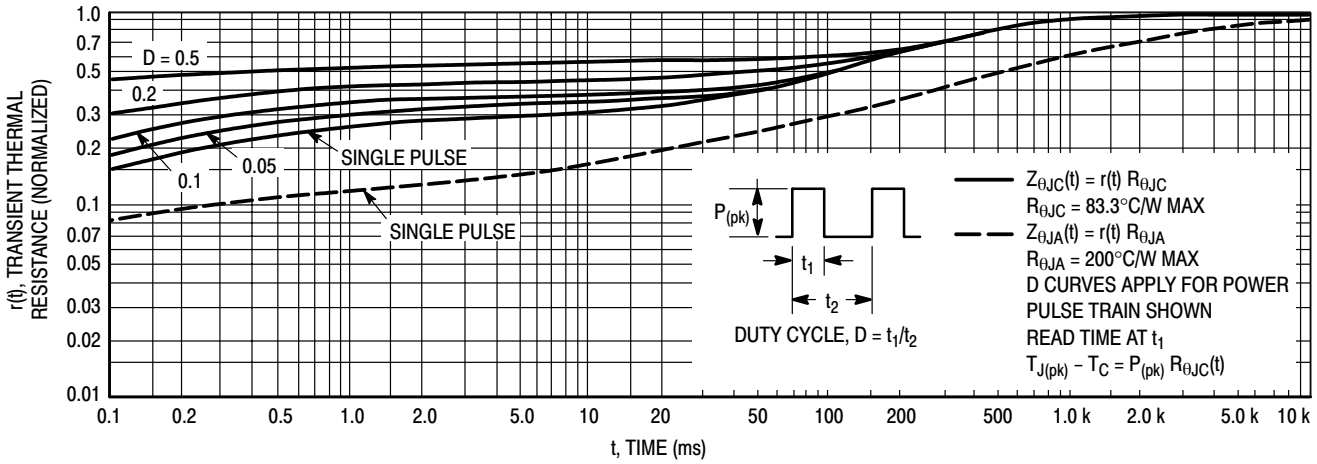


Figure 13. Thermal Response

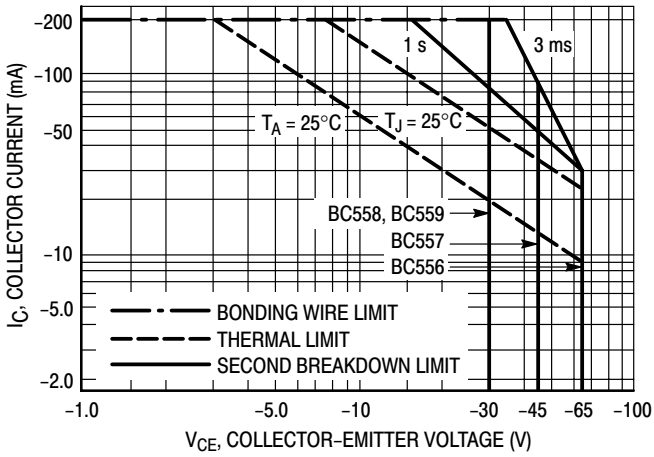


Figure 14. Active Region Safe Operating Area

The safe operating area curves indicate I_C-V_{CE} limits of the transistor that must be observed for reliable operation. Collector load lines for specific circuits must fall below the limits indicated by the applicable curve.

The data of Figure 14 is based upon $T_{J(pk)} = 150°C$; T_C or T_A is variable depending upon conditions. Pulse curves are valid for duty cycles to 10% provided $T_{J(pk)} \leq 150°C$. $T_{J(pk)}$ may be calculated from the data in Figure 13. At high case or ambient temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by the secondary breakdown.

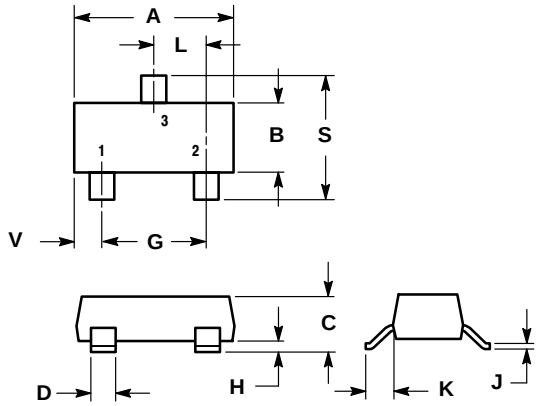
ORDERING INFORMATION

Device	Marking	Package	Shipping†
BC856ALT1	3A	SOT−23	3,000 / Tape & Reel
BC856ALT3	3A	SOT−23	10,000 / Tape & Reel
BC856BLT1	3B	SOT−23	3,000 / Tape & Reel
BC856BLT1G	3B	SOT−23 (Pb−Free)	
BC856BLT3	3B	SOT−23	10,000 / Tape & Reel
BC857ALT1	3E	SOT−23	3,000 / Tape & Reel
BC857BLT1	3F	SOT−23	3,000 / Tape & Reel
BC857BLT3	3F	SOT−23	10,000 / Tape & Reel
BC857BLT3G	3F	SOT−23 (Pb−Free)	
BC857CLT1	3G	SOT−23	3,000 / Tape & Reel
BC857CLT1G	3G	SOT−23 (Pb−Free)	3,000 / Tape & Reel
BC858ALT1	3J	SOT−23	3,000 / Tape & Reel
BC858ALT1G	3J	SOT−23 (Pb−Free)	
BC858BLT1	3K	SOT−23	3,000 / Tape & Reel
BC858BLT1G	3K	SOT−23 (Pb−Free)	
BC858BLT3	3L	SOT−23	10,000 / Tape & Reel
BC858CLT1	3L	SOT−23	3,000 / Tape & Reel
BC858CLT1G	3L	SOT−23 (Pb−Free)	
BC858CLT3	3L	SOT−23	10,000 / Tape & Reel
BC858CLT3G	3L	SOT−23 (Pb−Free)	
BC859BLT1	4B	SOT−23	3,000 / Tape & Reel
BC859BLT3	4B	SOT−23	10,000 / Tape & Reel
BC859CLT1	4C	SOT−23	3,000 / Tape & Reel
BC859CLT3	4C	SOT−23	10,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−09
ISSUE AI

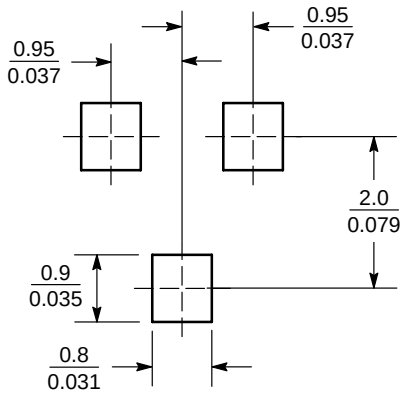


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01, −02, AND −06 OBSOLETE, NEW STANDARD 318−09.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0385	0.0498	0.99	1.26
D	0.0140	0.0200	0.36	0.50
G	0.0670	0.0826	1.70	2.10
H	0.0040	0.0098	0.10	0.25
J	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
V	0.0177	0.0236	0.45	0.60

STYLE 6:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
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Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

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Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.